

# HSM2693A

## Silicon Epitaxial Planar Diode for Tuner Band Switch

# HITACHI

Preliminary  
Rev. 2  
Jun. 1993

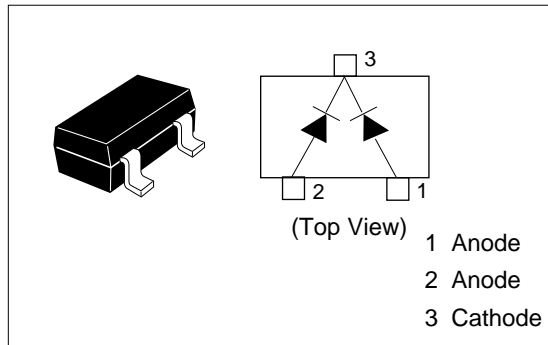
### Features

- Low forward resistance. ( $r_f=0.9\Omega$  max)
- Low capacitance. ( $C=1.2\text{pF}$  max)
- MPAK package is suitable for high density surface mounting and high speed assembly.

### Ordering Information

Type No.	Laser Mark	Package Code
HSM2693A	B 4	MPAK

### Pin Arrangement



### Absolute Maximum Ratings ( $T_a = 25^\circ\text{C}$ )

Item	Symbol	Value	Unit
Reverse voltage	$V_R$	35	V
Power dissipation	$p_d^*$	150	mW
Junction temperature	$T_j$	125	$^\circ\text{C}$
Storage temperature	$T_{stg}$	-45 to +125	$^\circ\text{C}$
Operation temperature	$T_{opr}$	-20 to +60	$^\circ\text{C}$

\* Two device total

### Electrical Characteristics ( $T_a = 25^\circ\text{C}$ ) \*

Item	Symbol	Min	Typ	Max	Unit	Test Condition
Reverse voltage	$V_R$	35	—	—	V	$I_R = 10 \mu\text{A}$
Reverse current	$I_R$	—	—	50	nA	$V_R = 25 \text{V}$
Forward voltage	$V_F$	—	—	1.0	V	$I_F = 10 \text{mA}$
Capacitance	C	—	—	1.2	pF	$V_R = 6 \text{V}, f = 1 \text{MHz}$
Forward resistance	$r_f$	—	—	0.9	$\Omega$	$I_F = 2\text{mA}, f = 100 \text{MHz}$

\* Per one device

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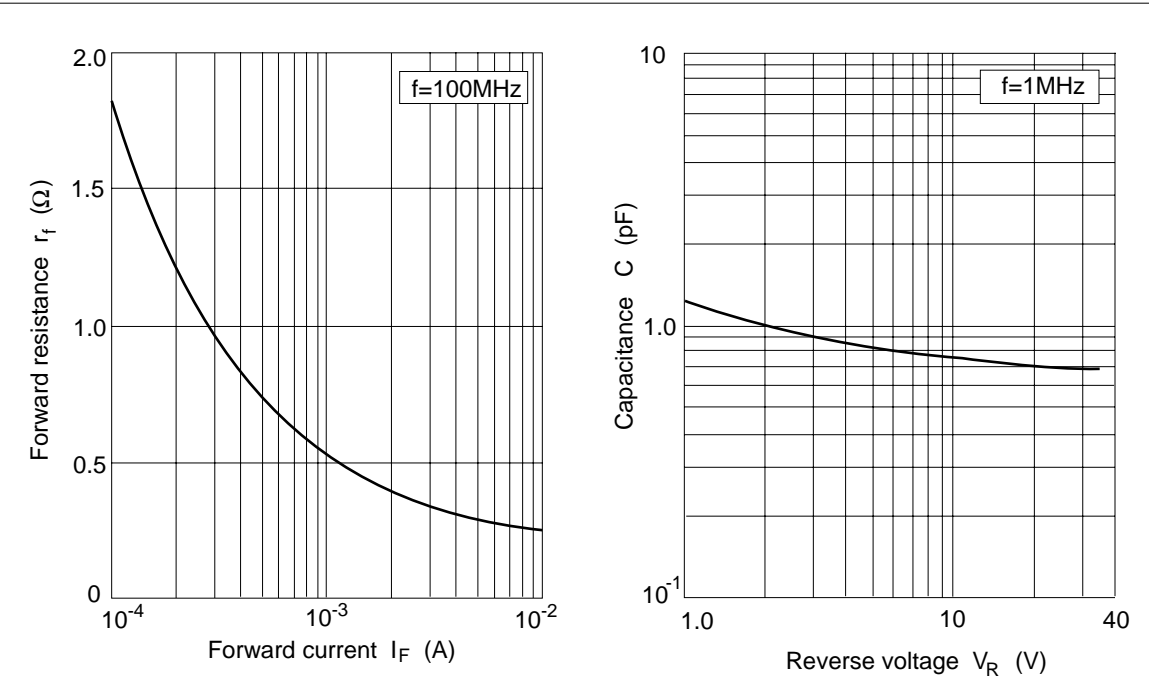


Fig.1 Forward resistance Vs. Forward current

Fig.2 Capacitance Vs. Reverse voltage

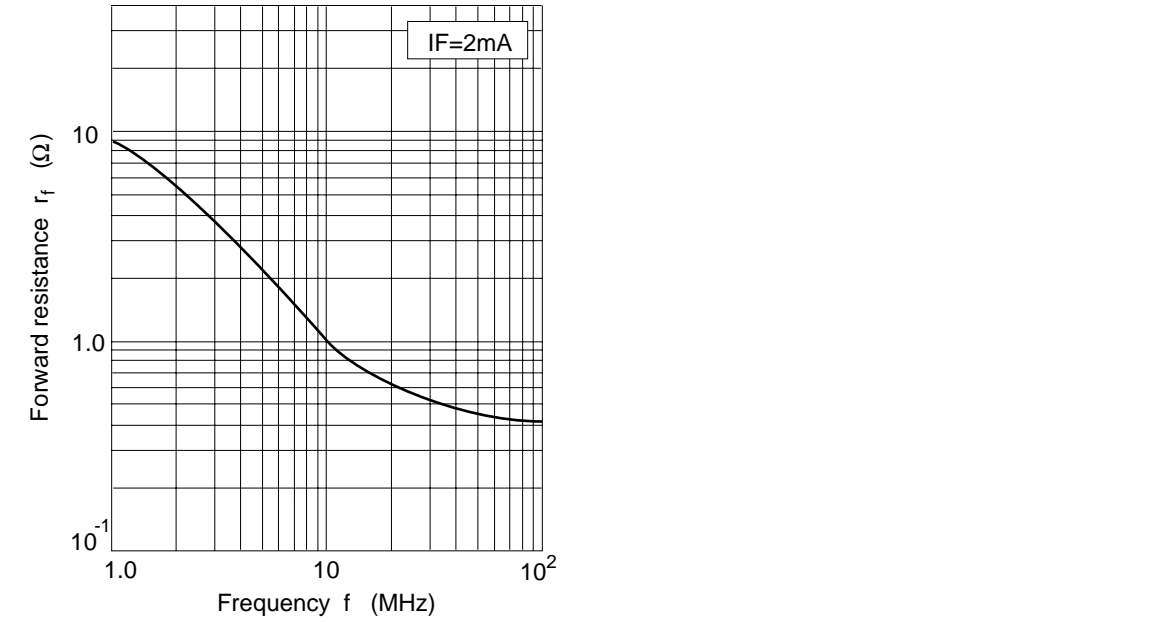


Fig.3 Forward resistance Vs. Frequency

### Package Dimensions

Unit: mm

